

L Number	Hits	Search Text	DB	Time stamp
-	2248	((438/199) or (438/135) or (438/153) or (438/154) or (438/201) or (438/627) or (257/204)).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:10
-	560	((438/199) or (438/135) or (438/153) or (438/154) or (438/201) or (438/627) or (257/204)).CCLS.) and (BPSG or PSG or glass)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/12 10:48
-	2820	gate and (oxide same barrier) and (BPSG or PSG or glass)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/13 14:19
-	5227	(CMOS) and (oxide same (furnace or photoexcitation or (photo near excitation) or microwave or ozone or steam or plasma))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:12
-	4348	(CMOS) and (oxide same (furnace and photoexcitation or (photo near excitation) and microwave and ozone and steam or plasma))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:13
-	4348	(CMOS) and (oxide same (furnace and photoexcitation and microwave and ozone and steam or plasma))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:20
-	0	(CMOS) and (oxide same (furnace and photoexcitation and microwave and ozone and steam and plasma))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:20
-	1	(CMOS) and (oxide same (photoexcitation))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:47
-	0	(oxygen near source) same (photoexcitation)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:49
-	102	oxide same photoexcitation	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:50
-	17	((silicon near oxide) same photoexcitation) or (silicon same oxide same photoexcitation)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 14:18
-	2893	((silicon near oxide) same steam) or (silicon same oxide same steam)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 13:58
-	1514	((silicon near oxide) same steam) or (silicon same oxide same steam) and CMOS	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 14:08

-	898	((silicon near oxide) same microwave) or (silicon same oxide same microwave)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 14:41
-	1738	((silicon near oxide) same ozone) or (silicon same oxide same ozone)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 14:42
-	265	((silicon near oxide) same ozone) or (silicon same oxide same ozone)) and CMOS	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/14 14:42